

3. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 1, comprising SF_6 , NF_3 , and an inert gas.

4. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 1, comprising SF_6 , F_2 , NF_3 , and an inert gas.

5. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 1, wherein the inert gas is at least one selected from the group consisting of He, Ne, Ar, Xe, Kr and N_2 .

6. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 5, wherein the inert gas is at least one selected from the group consisting of He, Ar, and N_2 .

7. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 1, wherein F_2 and/or NF_3 is from 0.01 to 5 and the inert gas is from 0.01 to 500 in terms of the volume ratio assuming that SF_6 is 1.

8. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 7, wherein F_2 and/or NF_3 is from 0.1 to 1.5 and the inert gas is from 0.1 to 30 in terms of the volume ratio assuming that SF_6 is 1.

9. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 1, which contains at least one gas selected from the group consisting of perfluorocarbon, hydrofluorocarbon, perfluoroether and hydrofluoroether.

PRELIMINARY AMENDMENT
National Stage Entry of PCT/JP01/06164
Q60716

10. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 9, wherein the perfluorocarbon and hydrofluorocarbon each has from 1 to 4 carbon atoms and the perfluoroether and hydrofluoroether each has from 2 to 4 carbon atoms.

12. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 11, comprising an oxygen-containing gas, an inert gas, SF_6 , and F_2 .

13. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 11, comprising an oxygen-containing gas, an inert gas, SF_6 , and NF_3 .

14. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 11, comprising an oxygen-containing gas, an inert gas, SF_6 , F_2 and NF_3 .

15. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 11, wherein the oxygen-containing gas is at least one selected from the group consisting of O_2 , O_3 , N_2O , NO , NO_2 , CO and CO_2 .

16. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 15, wherein the oxygen-containing gas is O_2 and/or N_2O .

17. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 11, wherein the inert gas is at least one selected from the group consisting of He, Ne, Ar, Xe, Kr and N_2 .

18. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 17, wherein the inert gas is at least one selected from the group consisting of He, Ar, and N₂.

19. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 11, wherein F₂ and/or NF₃ is from 0.01 to 5, the oxygen-containing gas is from 0.01 to 5 and the inert gas is from 0.01 to 500 in terms of the volume ratio assuming that SF₆ is 1.

20. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 19, wherein F₂ and/or NF₃ is from 0.1 to 1.5, the oxygen-containing gas is from 0.1 to 1.5 and the inert gas is from 0.1 to 30 in terms of the volume ratio assuming that SF₆ is 1.

21. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 11, which contains at least one gas selected from the group consisting of perfluorocarbon, hydrofluorocarbon, perfluoroether and hydrofluoroether.

22. (Amended) The cleaning gas for semiconductor production equipment as claimed in claim 21, wherein the perfluorocarbon and hydrofluorocarbon each has from 1 to 4 carbon atoms and the perfluoroether and hydrofluoroether each has from 2 to 4 carbon atoms.

23. (Amended) A method for cleaning semiconductor production equipment, comprising use of the cleaning gas as claimed in claim 1.

PRELIMINARY AMENDMENT
National Stage Entry of PCT/JP01/06164
Q60716

24. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 23, wherein the cleaning gas as claimed in claim 1 is excited to produce plasma and the deposits in the semiconductor production equipment are removed in the plasma.

25. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 24, wherein the excitation source for the plasma is a microwave.

26. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 23, wherein the cleaning gas as claimed in claim 1 is used at a temperature range of 50 to 500°C.

27. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 23, wherein the cleaning gas as claimed in claim 1 is used at a temperature range of 200 to 500°C in a plasmaless system.

28. (Amended) A method for cleaning semiconductor production equipment, comprising use of the cleaning gas as claimed in claim 11.

29. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 28, wherein the cleaning gas as claimed in claim 11 is excited to produce plasma and the deposits in the semiconductor production equipment are removed in the plasma.

30. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 29, wherein the excitation source for the plasma is a microwave

PRELIMINARY AMENDMENT
National Stage Entry of PCT/JP01/06164
Q60716

31. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 28, wherein the cleaning gas as claimed in claim 11 is used at a temperature range of 50 to 500°C.

32. (Amended) The method for cleaning semiconductor production equipment as claimed in claim 28, wherein the cleaning gas as claimed in claim 11 is used at a temperature range of 200 to 500°C in a plasmaless system.

34. (Amended) The method for producing a semiconductor device as claimed in claim 33, wherein the fluorocompound is at least one compound selected from the group consisting of HF, SiF₄, SF₆, SF₄, SOF₂, SO₂F₂, and WF₆.

36. (Amended) The method for producing a semiconductor device as claimed in claim 35, wherein the fluorocompound is at least one compound selected from the group consisting of HF, SiF₄, SF₆, SF₄, SOF₂, SO₂F₂, and WF₆.